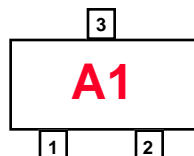
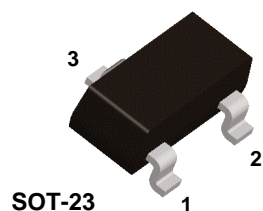
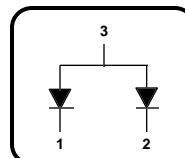


BAW56


CONNECTION DIAGRAMS


High Conductance Ultra Fast Diode

Sourced from Process 1P. See BAV99 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
W_{IV}	Working Inverse Voltage	70	V
I_O	Average Rectified Current	200	mA
I_F	DC Forward Current	600	mA
i_f	Recurrent Peak Forward Current	700	mA
$i_{f(surge)}$	Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 microsecond	1.0 2.0	A A
T_{stg}	Storage Temperature Range	-55 to +150	°C
T_J	Operating Junction Temperature	150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		BAW56	
P_D	Total Device Dissipation Derate above 25°C	350	mW
		2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

High Conductance Ultra Fast Diode

(continued)

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
B_V	Breakdown Voltage	$I_R = 5.0 \mu\text{A}$	85		V
I_R	Reverse Current	$V_R = 70 \text{ V}$ $V_R = 25 \text{ V}, T_A = 150^\circ\text{C}$ $V_R = 70 \text{ V}, T_A = 150^\circ\text{C}$		2.5 30 50	μA μA μA
V_F	Forward Voltage	$I_F = 1.0 \text{ mA}$ $I_F = 10 \text{ mA}$ $I_F = 50 \text{ mA}$ $I_F = 150 \text{ mA}$		715 855 1.0 1.25	mV mV V V
C_O	Diode Capacitance	$V_R = 0, f = 1.0 \text{ MHz}$		2.0	pF
T_{RR}	Reverse Recovery Time	$I_F = I_R = 10 \text{ mA}, I_{RR} = 1.0 \text{ mA},$ $R_L = 100\Omega$		6.0	nS
V_{FM}	Peak Forward Voltage	$I_F = 10 \text{ mA}, t_r = 20 \text{ nS}$		1.75	V